

# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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 APPLICANT  
QI XIANG

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July 17, 2003

 GROUP  
To be assigned

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
SWC		US	20020123167A1	09/2002	Fitzgerald	
		US	6,407,406 B1	7/2002	Tezuka	
		US	6,214,653 B1	04/2001	Chen et al	
		US	6,313,486 B1	11/2001	Kencke et al	
		US	0,008,284 A1	7/2001	Huang	
		US	6,251,751 B1	6/2001	Chu et al	
		US	0,003,269 A1	6/2001	Wu et al	
		US	5,759,898	6/1998	Ek et al	
		US	0,024,884 A1	9/2001	Fitzgerald	
		US	6,039,803	3/2000	Fitzgerald et al	
		US	0,016,383 A1	8/2001	Chen et al	
		US	6,180,490 B1	1/2001	Vassiliev et al	
		US	6,300,172 B1	10/2001	Ang et al	
	SWC		US	6,207,530 B1	3/2001	Hsu et al
		US				

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
SWC		Shallow Trench Isolation, "Trench Isolation," <a href="http://courses.nus.edu.sg/course/phy/&gt;pgs.1-4">http://courses.nus.edu.sg/course/phy/&gt;pgs. 1-4</a>
		Hitachi America, Ltd., Semiconductor Equipment Group, "Customizable Shallow Trench Isolation," <a href="http://www.hitachi.com/semiequipment/sti.html/&gt;pg.1">http://www.hitachi.com/semiequipment/sti.html/&gt;pg 1</a>
		SNP Applications/Shallow Trench Isolation (STI), "Shallow Trench Isolation (STD)," <a href="http://www.surfaceinterface.com/snpappsSTI.html/&gt;">http://www.surfaceinterface.com/snpappsSTI.html/&gt;</a> , pgs 1-2
SWC		Institute of Microelectronics - Deep Submicron - Shallow Trench Isolation, "Shallow Trench Isolation Module Development", <a href="http://www.ime.org.sg/deep_trench.htm/&gt;">http://www.ime.org.sg/deep_trench.htm/&gt;</a> , pgs. 1-2

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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		US			
		US			
		US			
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		US			
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FOREIGN PATENT DOCUMENTS						
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						Yes      No

OTHER ARTS (including Author, Title, Date, Patent, Paper, Etc.)		
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
SWC		David Lammers, "MIT spinout preps commercial strained silicon", Oct. 22, 2001, <a href="http://www.eetimes.com/story/OEG20011022S0078/">http://www.eetimes.com/story/OEG20011022S0078/</a> , pgs. 1-5
		IBM's Strained Silicon Breakthrough Image Page, June 8, 2001, <a href="http://www.research.ibm.com/resources/press/strainedsilicon/">http://www.research.ibm.com/resources/press/strainedsilicon/</a> , pgs. 1-2
		Dennis Sellers, "It isn't just IBM that has 'strained silicon' technology", June 14, 2001, <a href="http://maccentral.macworld.com/news/0106/14.silicon.shtml/">http://maccentral.macworld.com/news/0106/14.silicon.shtml/</a> , pgs. 1-5
		Matthew French, "Amber Wave Systems 'strained silicon' significant for semiconductor industry", August 6, 2001, <a href="http://www.mass.../displaydetail.asp?/">http://www.mass.../displaydetail.asp?/</a> , pgs. 1-3
		Richard Ball, "Strained silicon wafers boost FET speed 80 per cent at US start-up", Electronics Weekly Archive, pg. 1
		Orla Higgins, Press Release, "Amber Wave Systems Corporation Announces Availability of Breakthrough Strained Silicon Technology", October 22, 2001, pgs. 1-4
SWC		Mark A. Wolf, Pres Release, Amberwave Announces Strained Silicon Technology Available Immediately, June 8, 2001, pg. 1

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